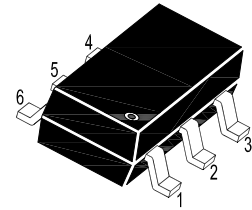
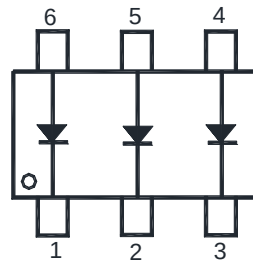


MMBD4448D

Silicon Epitaxial Planar Switching Diode

Fast Switching Diode



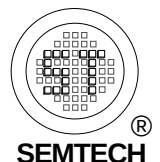
1. Cathode 2. Cathode 3. Cathode
4. Anode 5. Anode 6. Anode
Marking Code: SK
SOT-26 Plastic package

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

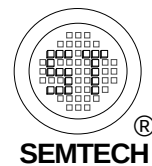
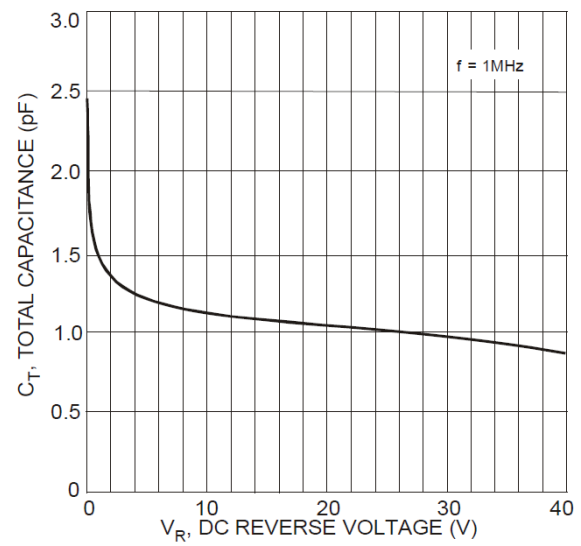
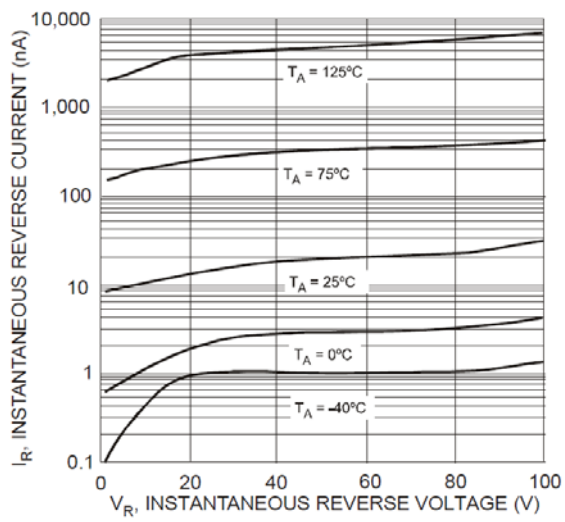
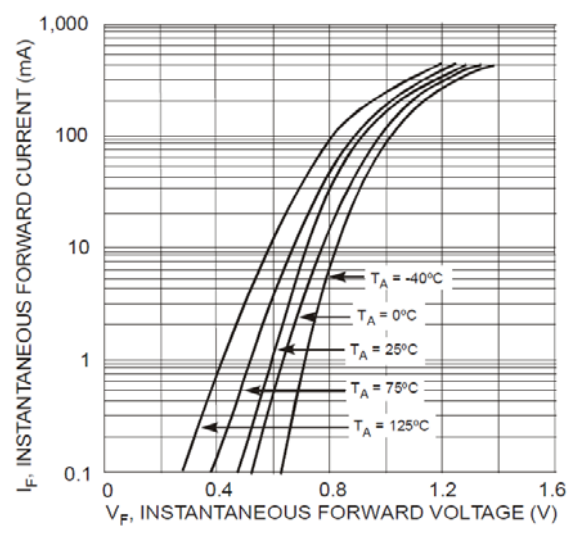
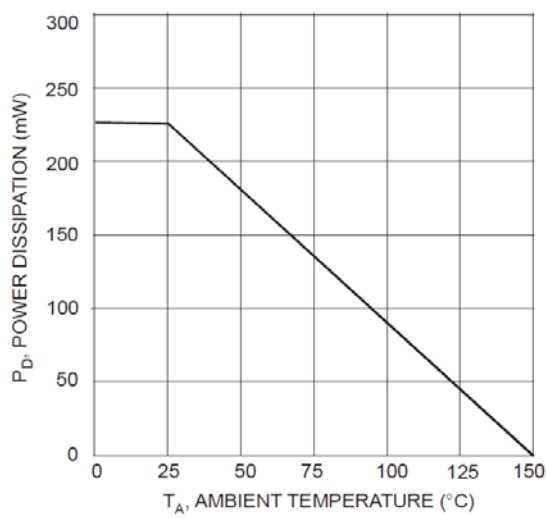
Parameter	Symbol	Value	Unit
Peak Reverse Voltage	V_{RM}	100	V
Reverse Voltage	V_R	80	V
Average Rectified Forward Current	$I_{F(AV)}$	250	mA
Forward Continuous Current	I_{FM}	500	mA
Non-Repetitive Peak Forward Surge Current (at $t = 1\ \mu\text{s}$)	I_{FSM}	4	A
Power Dissipation	P_d	350	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 65 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
Reverse Breakdown Voltage at $I_R = 100\ \mu\text{A}$	$V_{(BR)R}$	80	-	V
Forward Voltage at $I_F = 5\ \text{mA}$ at $I_F = 10\ \text{mA}$ at $I_F = 100\ \text{mA}$ at $I_F = 150\ \text{mA}$	V_F	0.62 - - -	0.72 0.855 1 1.25	V
Reverse Leakage Current at $V_R = 70\ \text{V}$ at $V_R = 20\ \text{V}$ at $V_R = 70\ \text{V}$, $T_J = 150^\circ\text{C}$ at $V_R = 25\ \text{V}$, $T_J = 150^\circ\text{C}$	I_R	- - - -	100 25 50 30	nA nA μA μA
Total Capacitance at $V_R = 6\ \text{V}$, $f = 1\ \text{MHz}$	C_{tot}	-	3.5	pF
Reverse Recovery Time at $I_F = I_R = 5\ \text{mA}$, $V_R = 6\ \text{V}$	t_{rr}	-	4	ns



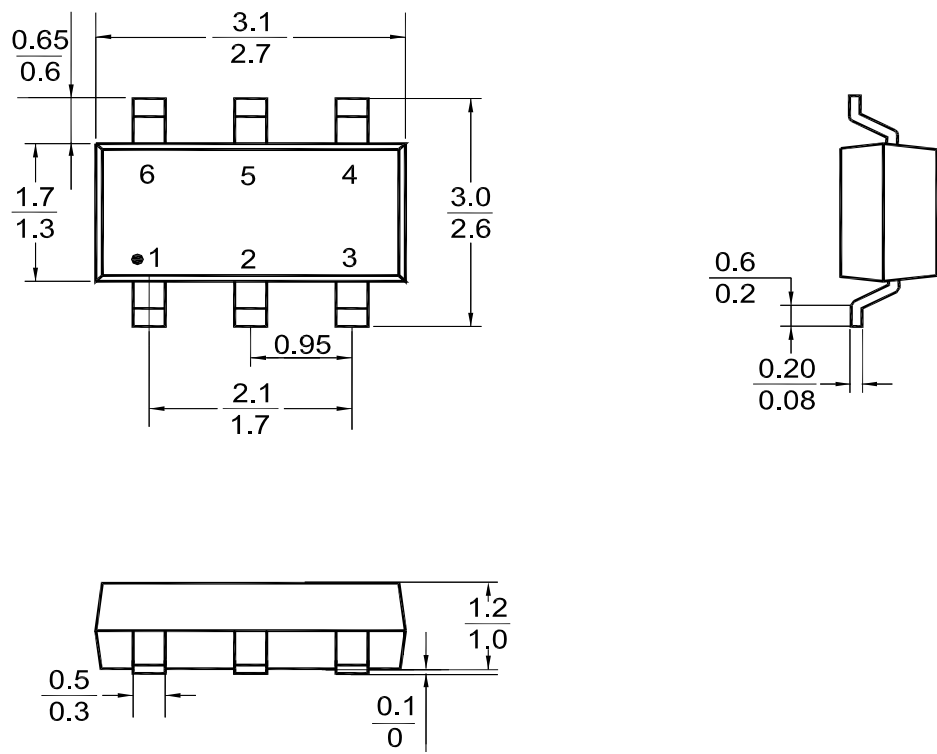
MMBD4448D



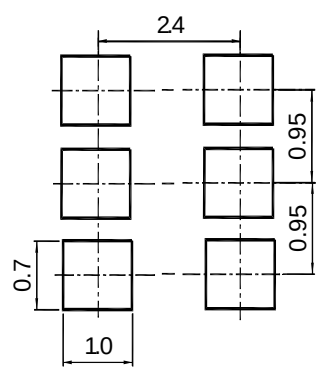
MMBD4448D

Package Outline Dimensions (Units: mm)

SOT-26



Recommended Soldering Footprint



Packing information

Package	Tape Width (mm)	Pitch		Reel Size		Per Reel Packing Quantity
		mm	inch	mm	inch	
SOT-26	8	4 ± 0.1	0.157 ± 0.004	178	7	3,000

